







IFN146 Dual Matched N-Channel JFET

Features

• InterFET N0450H Geometry

• Low Noise: 1.1 nV/VHz Typical

• High Gain: 30mS Typical

· RoHS Compliant

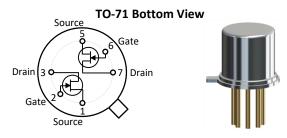
• SMT, TH, and Bare Die Package options.

Applications

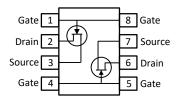
- · Low-Noise Audio Amplifier
- · Differential Amplifier
- Replacement for Japanese 2SK146

Description

The -50V InterFET IFN146 is a low noise high gain replacement for the Japanese 2SK146 JFET. Gate leakages are typically less than 50pA at room temperatures. The TO-71 package is hermetically sealed and suitable for military applications.



SOIC8 Top View





Product Summary

Parameters		IFN146 Min	Unit	
BV _{GSS}	Gate to Source Breakdown Voltage	-40	V	
I _{DSS}	Drain to Source Saturation Current	30 (max)	mA	
V _{GS(off)}	Gate to Source Cutoff Voltage	-0.3	V	
GFS	Forward Transconductance	20	mS	

Ordering Information Custom Part and Binning Options Available

Part Number	Description	Case	Packaging
IFN146	Through-Hole	TO-71	Bulk
SMP146	Surface Mount	SOIC8	Bulk
	7" Tape and Reel: Max 500 Pieces		Minimum 500 Pieces
SMP146TR	13" Tape and Reel: Max 2,500 Pieces	SOIC8	Tape and Reel
IFN146COT	Chip Orientated Tray (COT Waffle Pack)	СОТ	400/Waffle Pack
IFN146CFT	Chip Face-up Tray (CFT Waffle Pack)	CFT	400/Waffle Pack



Disclaimer: It is the Buyers responsibility for designing, validating and testing the end application under all field use cases and extreme use conditions. Guaranteeing the application meets required standards, regulatory compliance, and all safety and security requirements is the responsibility of the Buyer. These resources are subject to change without notice.









Electrical Characteristics

Maximum Ratings (@ T_A = 25°C, Unless otherwise specified)

	Parameters	Value	Unit
V_{RGS}	Reverse Gate Source and Gate Drain Voltage	-40	V
I _{FG}	Continuous Forward Gate Current	10	mA
PD	Continuous Device Power Dissipation	375	mW
Р	Power Derating	3	mW/°C
Tı	Operating Junction Temperature	-55 to 125	°C
T _{STG}	Storage Temperature	-65 to 200	°C

Static Characteristics (@ TA = 25°C, Unless otherwise specified)

			IFN146		
	Parameters	Conditions	Min	Max	Unit
V _{(BR)GSS}	Gate to Source Breakdown Voltage	V _{DS} = 0V, I _G = -1μA	-40		V
I _{GSS}	Gate to Source Reverse Current	$V_{GS} = -30V$, $V_{DS} = 0V$, $T_A = 25$ °C $V_{GS} = -30V$, $V_{DS} = 0V$, $T_A = 150$ °C		-1 -1	nA μA
V _{GS(OFF)}	Gate to Source Cutoff Voltage	$V_{DS} = 10V, I_{D} = 1\mu A$	-0.3	-1.2	V
I _{DSS}	Drain to Source Saturation Current	$V_{GS} = 0V$, $V_{DS} = 10V$ (Pulsed)		30	mA

Dynamic Characteristics (@ TA = 25°C, Unless otherwise specified)

			IFN146			
	Parameters	Conditions	Min	Тур	Max	Unit
G _{FS}	Forward Transconductance	$V_{DS} = 10V, V_{GS} = 0V, I_{DSS} = 5mA,$ f = 1kHz	20	30		mS
Ciss	Input Capacitance	V _{DS} = 10V, V _{GS} = 0V, f = 1kHz			75	рF
C _{rss}	Reverse Transfer Capacitance	V _{DS} = 10V, I _D = 0A, f = 1kHz			15	pF
NF	Noise Figure	V_{DS} = 10V, I_D = 5mA, R_G = 100 Ω , f = 1kHz		1		dB
V _{GS1} - V ₀	Differential Gate Source Voltage	V _{DS} = 10V, I _D = 5mA			20	mV



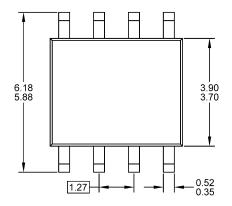


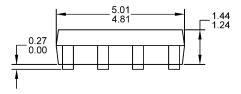


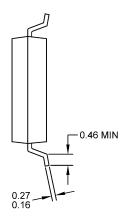


SOIC8 Mechanical and Layout Data

Package Outline Data

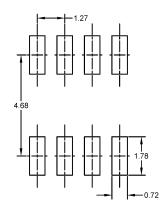






- 1. All linear dimensions are in millimeters.
- 2. Package weight approximately 0.21 grams
- 3. Molded plastic case UL 94V-0 rated
- For Tape and Reel specifications refer to InterFET CTC-021 Tape and Reel Specification, Document number: IF39002
- Bulk product is shipped in standard ESD shipping material
- 6. Refer to JEDEC standards for additional information.

Suggested Pad Layout



- 1. All linear dimensions are in millimeters.
- 2. The suggested land pattern dimensions have been provided for reference only. A more robust pattern may be desired for wave soldering.



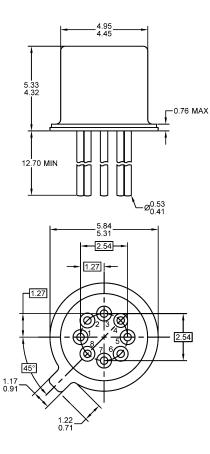






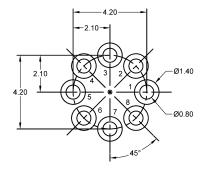
TO-71 Mechanical and Layout Data

Package Outline Data



- 1. All linear dimensions are in millimeters.
- Eight leaded device. Not all leads are shown in drawing views.
- 3. Some package configurations will not populate pin 8 and/or pin 4.
- 4. Package weight approximately 0.35 grams
- Bulk product is shipped in standard ESD shipping material
- 6. Refer to JEDEC standards for additional information.

Suggested Bent Lead Through-Hole Layout



- 1. All linear dimensions are in millimeters.
- 2. Pads 8 and/or pad 4 can be eliminated for devices with less pins.
- The suggested land pattern dimensions have been provided as an eight pin bent lead reference only. A more robust pattern may be desired for wave soldering or reduced pin count.

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